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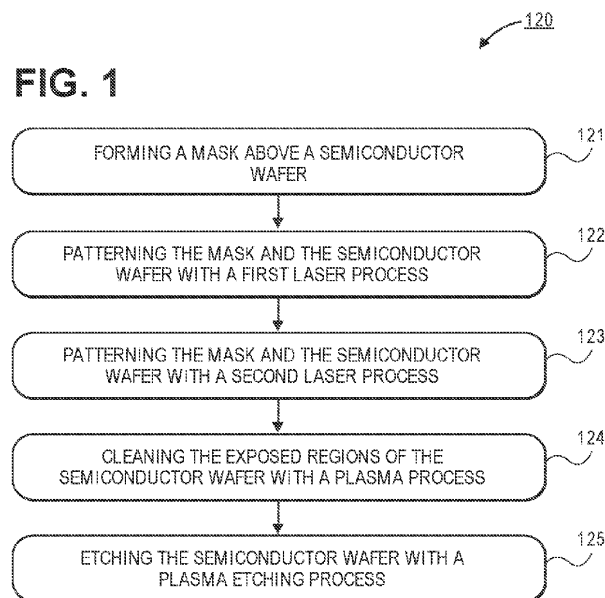
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(54) Title: LASER SCRIBING TRENCH OPENING CONTROL IN WAFER DICING USING HYBRID LASER SCRIBING AND PLASMA ETCH APPROACH

FIG. 1



(57) Abstract: An embodiment disclosed herein includes a method of dicing a wafer comprising a plurality of integrated circuits. In an embodiment, the method comprises forming a mask above the semiconductor wafer, and patterning the mask and the semiconductor wafer with a first laser process. The method may further comprise patterning the mask and the semiconductor wafer with a second laser process, where the second laser process is different than the first laser process. In an embodiment, the method may further comprise etching the semiconductor wafer with a plasma etching process to singulate the integrated circuits.

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